



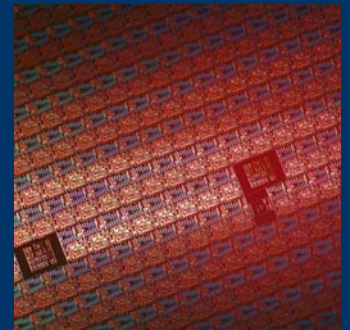
12th International EUV Initiative
Resist Technical Working Group
Feb, 26, 2009
SPIE, San Jose CA

Co-Chairs

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IEUVI Resist TWG February 26, 2009

Agenda

1:00 PM - 1:15 PM	Welcome and Introduction	<i>J. Georger, SEMATECH</i>
1:15 PM - 1:25 PM	Focus Topic: Addressing Pattern Collapse in EUV	<i>J. Georger, SEMATECH</i>
1:25 PM - 1:45 PM	Challenges Associated with Line Pattern Collapse for EUV Lithography	<i>S. Scheer, Tokyo Electron America</i>
1:45 PM - 2:05 PM	EUV Resist Pattern Collapse Status	<i>C. Koh, SEMATECH</i>
2:05 PM - 2:25 PM	Resist Pattern Collapse Failure: Quantifying Problem & Ways to Solve It	<i>C. Henderson, Georgia Tech University</i>
2:25 PM - 2:45 PM	How and Why Does Pattern Collapse Occur	<i>J. Iwashita, TOK</i>
2:45 PM - 3:05 PM	Pattern Collapse in EUV Resists	<i>S. Tarutani, Fujifilm</i>
3:05 PM - 3:20 PM	Break	
3:20 PM - 3:40 PM	Resist Outgassing WG Introduction	<i>E. Piscani, SEMATECH</i>
3:40 PM - 4:00 PM	OS1 Resist Outgassing Results at Multiple Sites	<i>C. Mbanaso, CNSE</i>
4:00 PM - 4:30 PM	Wrap-Up and Topics for Next Resist TWG Meeting	

Why Focus Topic on Pattern Collapse?



- EUV needs to achieve 22nm node capability and beyond for insertion into manufacturing.
 - RLS has received much attention in the industry and progress is being made, though more is required.
- As we continue to push EUV resolution toward 22nm hp, **Pattern Collapse** has been identified as the main failure mechanism limiting resolution, and acceptable process windows.

TWG Objective: Raise awareness of Resist Pattern Collapse Issue, and Provide Insight into Root Causes and Potential Solutions!

- Today's Speakers will share their thoughts and findings on driving forces of pattern collapse, current status, and impact of processing, resist material type, substrates, ancillaries, etc.....
- **Resist Outgassing**
 - Intro: EUV resist Outgassing WG
 - Update on multisite OS1 Outgassing results

Please don't hesitate to interact !